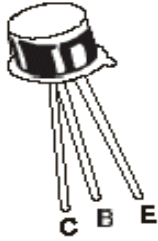


PNP SILICON PLANAR TRANSISTOR

2N995

TO-18

Metal Can Package



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless specified otherwise)

DESCRIPTION	SYMBOL	2N995	UNITS
Collector Emitter Voltage	V_{CEO}	15	V
Collector Base Voltage	V_{CBO}	20	V
Emitter Base Voltage	V_{EBO}	4	V
Collector Current Continuous	I_C	200	mA
Power Dissipation at $T_a = 25^\circ\text{C}$	P_D	0.36	W
at $T_c = 25^\circ\text{C}$		1.2	W
Operating And Storage Junction Temperature Range	T_j, T_{stg}	-65 to +200	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
Collector Emitter Voltage	V_{CEO}	$I_C = 1\text{mA}, I_B = 0$	15			V
Collector Base Voltage	V_{CBO}	$I_C = 10\mu\text{A}, I_E = 0$	20			V
Emitter Base Voltage	V_{EBO}	$I_C = 10\mu\text{A}, I_B = 0$	4			V
Collector Cut Off Current	I_{CBO}	$V_{CB} = 15\text{V}, I_E = 0$			5	nA
		$V_{CB} = 15\text{V}, T_a = 150^\circ\text{C}$			25	μA
Emitter leakage current	I_{EBO}	$V_{EB} = 4\text{V}, I_B = 0$			10	μA
Collector Emitter Saturation Voltage	$V_{CE(Sat)}$	$I_C = 10\text{mA}, I_B = 1\text{mA}$			0.2	V
Base Emitter Saturation Voltage	$V_{BE(Sat)}$	$I_C = 10\text{mA}, I_B = 1\text{mA}$			0.95	V
DC Current Gain	*hFE	$I_C = 1\text{mA}, V_{CE} = 1\text{V}$	25			
		$I_C = 20\text{mA}, V_{CE} = 1\text{V}$	35		140	
		$I_C = 50\text{mA}, V_{CE} = 1\text{V}$	25			

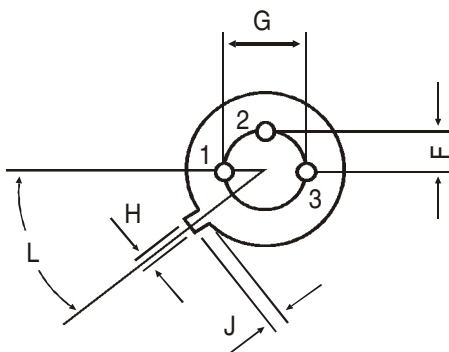
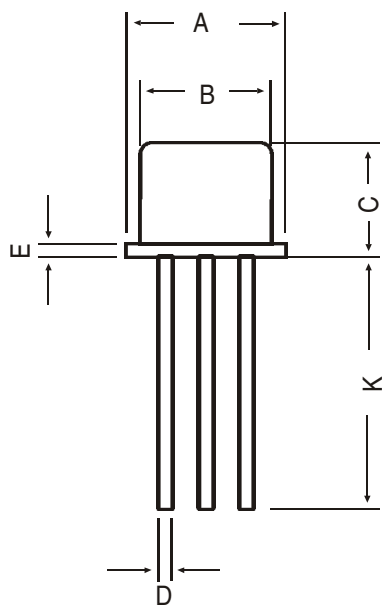
2N995
TO-18
Metal Can Package

DYNAMIC CHARACTERISTICS

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
Transistor Frequency	f_T	$I_C = 10\text{mA}$, $V_{CE} = 15\text{ V}$, $f = 100\text{ MHz}$	100			MHz
Input Capacitance	C_{ib}	$V_{BE} = 0.5\text{V}$, $I_C = 0$			11	pF
Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}$, $I_E = 0$			10	pF

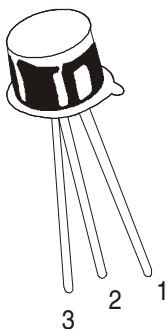
* Pulse Condition : Length $\leq 300\mu\text{S}$, Duty Cycle $\leq 1\%$

TO-18 Metal Can Package



All dimensions in mm.

DIM	MIN	MAX
A	5.24	5.84
B	4.52	4.97
C	4.31	5.33
D	0.40	0.53
E	—	0.76
F	—	1.27
G	—	2.97
H	0.91	1.17
J	0.71	1.21
K	12.70	—
L	45 DEG	



PIN CONFIGURATION

- 1. EMITTER
- 2. BASE
- 3. COLLECTOR

Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/ Qty	Size	Qty	Size	Qty	Gr Wt
TO-18	1K/polybag	350 gm/1 K pcs	3" x 7.5" x 7.5"	5K	17" x 15" x 13.5"	80K	34 kgs

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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